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Substitute for form 1449/PTO				Complete if Known		
				Application Number	10/581,950-Conf. #8737	
IN.	NFORMATION	1 DI	SCLOSURE	Filing Date	August 18, 2008	
l s	STATEMENT BY APPLICANT			First Named Inventor	Anderson	
				Art Unit	2872 2894	
	(Use as many sheets as necessary)			Examiner Name	D. T. Nguyen	
Sheet	1	of	1	Attorney Docket Number	GWS-008	

	U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ² (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
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	B1	WO-2005-057617 A3	06-23-2005	Great Wall Semiconductor		

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Examiner Signature		/Duy Nguyen/	Date Considered	06/02/2009			

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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